ARPA-E SWITCHES PROGRAM KICKOFF
SHERATON CRESCENT HOTEL
PHOENIX, AZ
JANUARY 23, 2014

LOCATION NOTES:
The General Session will take place in Crescent Room Salon A
Meals will be served buffet-style in Crescent Room Foyer
The Poster Session/Networking Reception will take place in Crescent Room Salon B

Time	Institution	Project Title	Presenters
7:30 – 8:00	**BREAKFAST & REGISTRATION**		
8:00 – 8:15	Welcome and Introductions		**T. Heidel**
8:15 – 8:30	SWITCHES Overview		**T. Heidel**
8:30 – 8:45	Introduction to Technology to Market		**D. Henshall**
8:45 – 9:00	**BREAK**		
9:00 – 9:15	**Monolith Semiconductor, Inc.**	Advanced Manufacturing and Performance Enhancements for Reduced-cost Silicon Carbide MOSFETs (AMPERES)	**K. Matocha**
9:15 – 9:30	**ASU**	Diamond Power Transistors Enabled by Phosphorus Doped Diamond	**R. Nemanich**
9:30 – 9:45	**Michigan State University**	Diamond Diode and Transistor Devices	**T. Grotjohn**
9:45 – 10:00	**Discussion**		**T. Heidel**
10:00 – 10:15	**BREAK**		
10:15 – 10:30	**Fairfield Crystal Technology, LLC**	High-quality, low-cost GaN single crystal substrates for high-power devices	**S. Wang**
10:30 – 10:45	**Kyma Technologies, Inc.**	Transformational GaN Substrate Technology	**J. Leach**
10:45 – 11:00	**SixPoint Materials, Inc.**	GaN homoepitaxial wafers for vertical high-power devices grown by vapor phase epitaxy on low-cost, high-quality ammonothermal GaN substrates	**T. Hashimoto**
11:00 – 11:15	**BREAK**		
11:15 – 11:30	**Microlink**	High-Power Vertical-Junction Field-Effect Transistors Fabricated on Low-Dislocation-Density GaN by Epitaxial Lift-Off	**C. Youtsey**
11:30 – 11:45	**Soraa, Inc.**	Large Area, Low Cost Bulk GaN Substrates for Power Electronics	**M. D'Evelyn**
11:45 – 12:00	**iBeam Materials, Inc.**	Epitaxial GaN on flexible metal tapes for low-cost transistor devices	**V. Matias**
12:00 – 12:15	**Discussion**		**T. Heidel**
12:15 – 1:15	**LUNCH**		

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Time	Institution	Project Title	Presenters
1:15 – 2:00	**Panel Discussion: Introduction to other Government WBG efforts**		
2:00 – 2:15	**Avogy, Inc.**	Vertical GaN transistors on bulk GaN substrates	**I. Kizilyalli**
2:15 – 2:30	**University of Notre Dame**	PolarJFET - a novel vertical GaN power transistor concept	**H. Xing**
2:30 – 2:45	**University of California, Santa Barbara**	Ultimate Switches (US)	**U. Mishra**
14:45 – 3:00	**BREAK**		
3:00 – 3:15	**Columbia University**	Vertical GaN power transistors using controlled spalling for substrate heterogeneity	**K. Shepard**
4:15 – 3:30	**HRL Laboratories, LLC**	Low-Cost Gallium Nitride Vertical Transistor Switch	**R. Chu**
3:30 – 3:45	**Discussion**		**T. Heidel**
3:45 – 4:00	**Program Director Wrap-up**		**T. Heidel**
4:00 – 6:00	**Poster Session & Networking**		